30V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

 $V_{(BR)DSS} = -30V$; $R_{DS(ON)} = 0.040\Omega$; $I_D = -6.7A$

DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



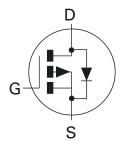
SO8

FEATURES

- · Low on-resistance
- · Fast switching speed
- · Low threshold
- · Low gate drive
- Low profile SOIC package

APPLICATIONS

- Disconnect switches
- Motor control



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP3A16N8TA	7″	12mm	500 units
ZXMP3A16N8TC	13"	12mm	2500 units

DEVICE MARKING

 ZXMP 3A16

PINOUT



Top View

ISSUE 2 - MAY 2007

SEMICONDUCTORS

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	-30	V
Gate Source Voltage	V _{GS}	±20	V
Continuous Drain Current V_{GS} =-10V; T_A =25°C (b) V_{GS} =-10V; T_A =70°C (b) V_{GS} =-10V; T_A =25°C (a)	I _D	-6.7 -5.4 -5.6	А
Pulsed Drain Current (c)	I _{DM}	-26	А
Continuous Source Current (Body Diode) (b)	I _S	-3.2	А
Pulsed Source Current (Body Diode) (c)	I _{SM}	-26	А
Power Dissipation at T _A =25°C (a) Linear Derating Factor	P _D	1.9 15.2	W mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	P _D	2.8 22.4	W mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	65	°C/W
Junction to Ambient (b)	$R_{\theta JA}$	45	°C/W

NOTES

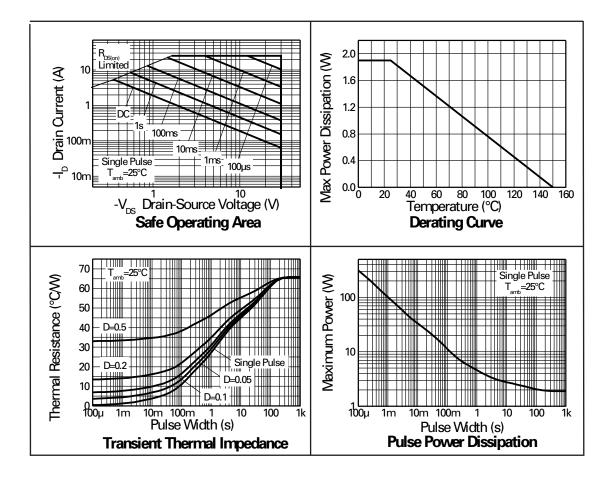
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions



⁽b) For a device surface mounted on FR4 PCB measured at t≤5 secs.

⁽c) Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width 10 μs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

CHARACTERISTICS



ZETEXSEMICONDUCTORS

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

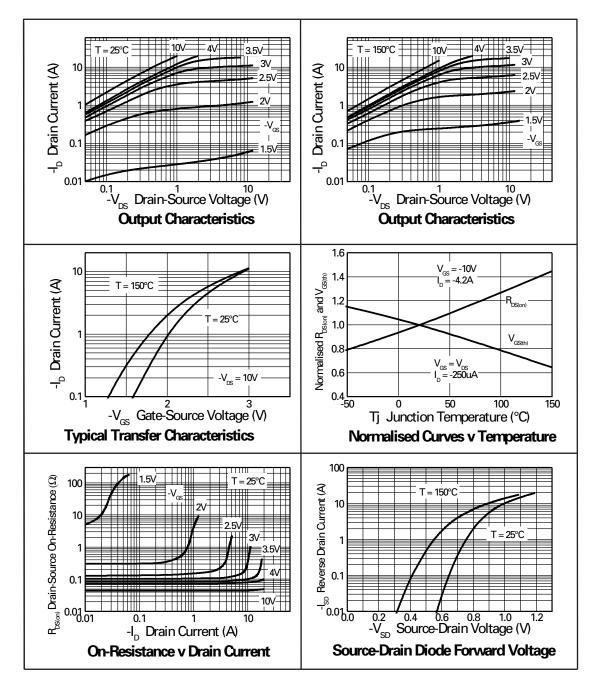
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS	
STATIC							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-30			V	I _D =-250μA, V _{GS} =0V	
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μΑ	V _{DS} =-30V, V _{GS} =0V	
Gate-Body Leakage	I _{GSS}			100	nA	V_{GS} = $\pm 20V$, V_{DS} = $0V$	
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	I _D =-250μA,V _{DS} = V _{GS}	
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.040 0.070	$\Omega \Omega$	V _{GS} =-10V, I _D =-4.2A V _{GS} =-4.5V, I _D =-3.4A	
Forward Transconductance (1)(3)	g _{fs}		9.2		S	V _{DS} =-15V,I _D =-4.2A	
DYNAMIC (3)							
Input Capacitance	C _{iss}		1022		pF		
Output Capacitance	Coss		267		pF	V _{DS} =-15 V, V _{GS} =0V, f=1MHz	
Reverse Transfer Capacitance	C _{rss}		229		pF		
SWITCHING(2) (3)							
Turn-On Delay Time	t _{d(on)}		3.8		ns		
Rise Time	t _r		6.5		ns	V _{DD} =-15V, I _D =-1A	
Turn-Off Delay Time	t _{d(off)}		37.1		ns	$R_G=6.0\Omega$, $V_{GS}=-10V$	
Fall Time	t _f		21.4		ns		
Gate Charge	Qg		17.2		nC	V _{DS} =-15V,V _{GS} =-5V, I _D =-4.2A	
Total Gate Charge	Q_g		29.6		nC	V _{DS} =-15V,V _{GS} =-10V, I _D =-4.2A	
Gate-Source Charge	Q _{gs}		2.8		nC		
Gate-Drain Charge	Q_{gd}		8.6		nC		
SOURCE-DRAIN DIODE							
Diode Forward Voltage (1)	V _{SD}		-0.85	-0.95	V	T _J =25°C, I _S =-3.6A, V _{GS} =0V	
Reverse Recovery Time (3)	t _{rr}		21.7		ns	T _J =25°C, I _F =-2A,	
Reverse Recovery Charge (3)	Q _{rr}		16.1		nC	di/dt= 100A/μs	

NOTES

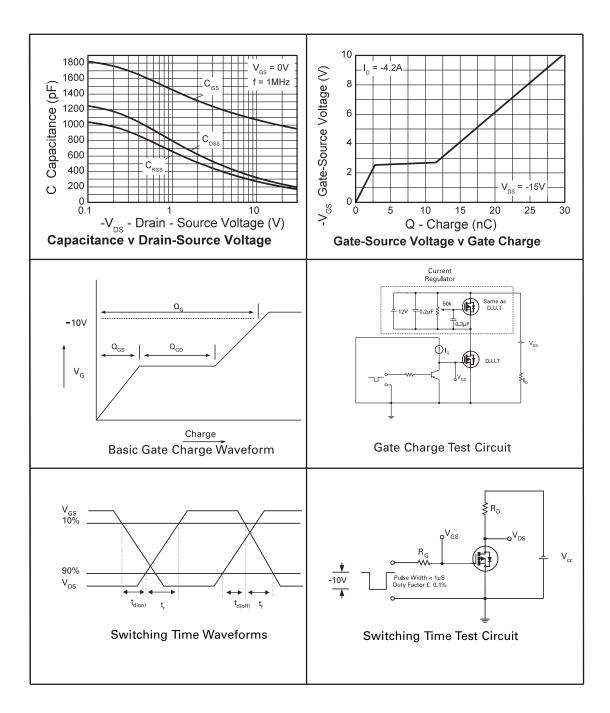
- (1) Measured under pulsed conditions. Width ${\leq}300\mu s.$ Duty cycle ${\leq}\,2\%$.
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.



CHARACTERISTICS









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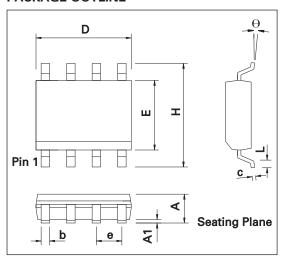
- "Preview"Future device intended for production at some point. Samples may be available
- "Active"Product status recommended for new designs
- "Last time buy (LTB)"Device will be discontinued and last time buy period and delivery is in effect
- "Not recommended for new designs"Device is still in production to support existing designs and production
- "Obsolete"Production has been discontinued

Datasheet status key:

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PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES APPROX IN MILLIMETERS

PACKAGE DIMENSIONS

DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
DIIVI	Min	Max	Min	Max	DIIVI	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069	е	1.27 BSC		0.050 BSC	
A1	0.10	0.25	0.004	0.010	b	0.33	0.51	0.013	0.020
D	4.80	5.00	0.189	0.197	С	0.19	0.25	0.008	0.010
Н	5.80	6.20	0.228	0.244	θ	0°	8°	0°	8°
Е	3.80	4.00	0.150	0.157	h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050	-	-	-	-	-

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